# Electronically Tunable Grounded and Floating Capacitance Multipliers Using a Single Active Element 

Nuttapon Seechaiya, ${ }^{1}$ Winai Jaikla $\left({ }^{1},{ }^{1}\right.$ Amornchai Chaichana $\left(\mathbb{C},{ }^{1}\right.$ Phamorn Silapan, ${ }^{2}$ Piya Supavarasuwat ${ }^{(1)},{ }^{1}$ and Peerawut Suwanjan ${ }^{1}$<br>${ }^{1}$ Department of Engineering Education, School of Industrial Education and Technology, King Mongkut's Institute of Technology Ladkrabang, Bangkok 10520, Thailand<br>${ }^{2}$ Department of Electrical Engineering, Faculty of Engineering and Industrial Technology, Silpakorn University, Nakhon Pathom 73000, Thailand<br>Correspondence should be addressed to Amornchai Chaichana; amornchai.ch@kmitl.ac.th

Received 29 January 2024; Revised 21 April 2024; Accepted 7 May 2024; Published 23 May 2024
Academic Editor: Manuela Minetti
Copyright © 2024 Nuttapon Seechaiya et al. This is an open access article distributed under the Creative Commons Attribution License, which permits unrestricted use, distribution, and reproduction in any medium, provided the original work is properly cited.


#### Abstract

A capacitance multiplier is an active circuit designed specifically to increase the capacitance of a passive capacitor to a significantly higher capacitance level. In this paper, the use of a voltage differencing differential difference amplifier (VDDDA), an electronically controllable active device for designing grounded and floating capacitance multipliers, is proposed. The capacitance multipliers proposed in this study are extremely simple and consist of a VDDDA, a resistor, and a capacitor. The multiplication factor ( $K_{c}$ ) can be electronically controlled by adjusting the external bias current $\left(I_{B}\right)$. It offers an easy way of controlling it by utilizing a microcontroller for modern analog signal processing systems. The multiplication factor has the potential to be adjusted to a value that is either less than or greater than one, hence widening the variety of uses. The grounded capacitance multiplier can be easily transformed into a floating one by utilizing Zc-VDDDA. PSpice simulation and experimentation with a VDDDA realized from commercially available integrated circuits were used to test the performance of the proposed capacitance multipliers. The multiplication factor is electronically adjustable, ranging in approximation from 0.56 to 13.94 . The operating frequency range is approximately three frequency decades. The realization of the lagging and leading phase shifters using the proposed capacitance multiplier is also examined and proven. The results reveal that the lagging and leading phase shifts are electronically tuned via the multiplication factor of the proposed capacitance multipliers.


## 1. Introduction

The invention of integrated circuits (ICs) has led to a significant development in worldwide technological advances, particularly in electrical, electronic, and communication systems. In the last half-century, there has been a persistent focus on research and development in integrated circuit design, especially in analog signal processing systems. Many techniques have been proposed in analog circuit design, where most approaches involve the combination of active devices alongside passive components, such as resistors or capacitors. The utilization of passive inductors in circuit design is widely considered less favored due to their large
size and the difficulties associated with adjusting the inductance value. Hence, employing capacitors in the design of analog signal processing circuits that involve frequency is deemed more suitable. A capacitor with a large capacitance value is needed in many applications, including lowfrequency filters [1, 2], sample and hold circuits [3], locked-in amplifiers [4], and sensor applications [5]. Variable capacitors are also fundamental devices in a wide range of wireless telecommunication systems, including voltagecontrol oscillators, tunable filters, matching circuits, and phase shifters [6]. Although the process of fabricating a capacitor within an integrated circuit is possible [6, 7], the high-value on-chip capacitors result in significant chip area
occupation, high absolute tolerances, and restricted capacitance adjustability [ $1,2,8$ ]. In order to handle the concerns mentioned above, the implementation of an active circuit known as the capacitance multiplier is employed. This active circuit combines a passive capacitor and/or a passive resistor. It has been designed to emulate the behavior of a significantly larger capacitor using a smaller capacitor. The parameter of the capacitance multiplier called the multiplication factor $\left(K_{c}\right)$ is normally adjustable. When it is used instead of the passive capacitor in circuit designs, the parameters of these circuits, such as the cutoff frequency, the oscillation frequency, and the phase shift, are consequently tunable.

The synthesis of electronically adjustable analog circuits is increasingly appealing in contemporary analog signal processing systems. Microcomputers or programmable devices are commonly utilized to provide intelligent and autonomous control of circuits. In recent times, there has been a surge in the popularity of employing active building blocks (ABBs) for the synthesis of analog circuits [9-12]. This trend can be attributed to the significant advantages it offers in terms of simplicity, flexibility, and versatility. Combining an ABB with just a few passive components, such as capacitors or resistors, gives several analog circuits with superior performance characteristics. Furthermore, using active components with high input and low output impedances during voltage-mode circuit synthesis can eliminate the need for additional voltage buffers at the input and output stages. Additionally, some ABB s with electronically controllable properties are essential for modern circuits, as stated above. Numerous analog circuits employing electronically controllable analog ABBs have been presented in the existing body of scholarly research. The voltage differencing differential difference amplifier (VDDDA) [13] is a contemporary and flexible analog building block that exhibits adaptability and versatility in various circuit designs for analog signal processing. This device integrates the characteristics of an operational transconductance amplifier (OTA) with electronic control and a differential difference amplifier (DDA) with lowoutput impedance and unity gain. As a result, the transconductance of VDDDA can be adjusted electronically by utilizing an external direct current bias current. The circuit parameters of the VDDDA-based system can be electrically controlled, including the current or voltage gain, cutoff or oscillation frequency, quality factor, and bandwidth. Moreover, it is common practice in circuit synthesis to include an integrator and passive simulator while incorporating a subtractor or adder. Hence, the existence of the DDA within VDDDA presents significant benefits in expediting the synthesis procedure. Moreover, the VDDDA exhibits a high impedance at both the input-voltage and output-current terminals while maintaining a low impedance at the output-voltage terminal.

Several implementations of capacitance multipliers using different ABBs have been reported in published works [14-54]. These utilized ABBs include operational amplifier (opamp), operational transconductance amplifier (OTA), voltage buffer, current conveyor (CCII), voltage-to-current
transducer (VCT), current operational amplifier (COA), current-controlled conveyor transconductance amplifier (CCCTA), modified current-feedback operational amplifier (MCFOA), voltage and current gain second generation current conveyor (VCG-CCII), differential voltage current conveyor transconductance amplifier (DV-CCTA), tunable four-terminal floating nullor (TFTFN), current control differential difference current conveyor (CCDDCC), dual-X second-generation current conveyor (DXCCII), voltage differencing current conveyor (VDCC), current follower transconductance amplifier (CFTA), fully balanced voltage differencing buffered amplifier (FB-VDBA), voltage differencing inverting buffered amplifier (VDIBA), current differencing transconductance amplifier (CDTA), current feedback operational amplifier (CFOA), third-generation current conveyor transconductance amplifier (CCIIITA), voltage conveyor (VCII), differential voltage buffer (DVB), operational transresistance amplifier (OTRA), current follower differential input transconductance amplifier (CFDITA), and VDDDA. There are two classifications of ABB-based capacitance multipliers: grounded ones [14, 16-18, 20-22, 24, 27, 28, 33, 37-41, 43-53] and floating ones $[15,18,19,23,25,26,29-32,34-36$, $40,42,46,54]$, as indicated in Table 1. Simple structures with a single ABB were proposed in $[14,20,24,28-31,40,42$, $45,49,52,53]$, unlike the capacitance multiplier in [15-19, 21-27, 32-41, 43, 44, 46-48, 50, 51, 54], which uses different kinds and more than one ABB . The resistor-less circuits were realized in $[16,18,19,23,26,27,29-33,35$, $37,41,45,46,51,53$ ], but using more than one resistor was needed for the capacitance multipliers realized in [ $14,15,20-22,24,25,28,34,36,38,40,43,44,47-50,52,54]$. The multiplication factor of the proposed capacitance multipliers in references $[14,15,20-22,24,25,28,36,38$, $40,43,47,49,50,54]$ cannot be electronically adjusted. In the given references $[16,20,21,24,33,36-38,40-43,49$, $50,52,53]$, the inability to adjust the multiplication factor to a value greater or less than one limits its widespread applicability. A recent grounded capacitance multiplier using one VDDDA, one MOS transistor, and one capacitor was proposed [51]. The multiplication factor can be electronically tuned to be greater or less than one. However, the multiplication factor is inversely proportional to the bias current, which implies that setting the bias current to a low value will result in a high multiplication factor, thereby distorting the OTA's output signal (in VDDDA). Moreover, this grounded capacitance multiplier structure is not easy to modify as a floating type. The results of this comparison study are summarized in Table 1 (Figures 1 and 2).

This paper proposes grounded and floating capacitance multipliers with an electronic tuning of the multiplier factor. The paper covers the following topics: a description of the circuit principle is shown in Section 2, including an overview of VDDDA, proposed electronically controllable capacitance multipliers, and the effect of nonideal properties of VDDDA. Section 3 presents the results of circuit simulations using the PSpice program and the prototype experiment. Section 4 demonstrates the application examples of the capacitance multipliers and their experimental results in the lagging and leading phase
Table 1: Comparison of existing capacitance multipliers using ABBs.

| Ref. | ABB | $R+C$ | Floating/grounded | Electronic tune | $K_{c}$ can be set to be greater or less than one | Supply (V) and power consumption (mW) | Testing | Technology |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| [14] | 1 opamp | $3+1$ | Grounded | No | Yes | NA | Experiment | IC |
| [15] | 4 CCII | $2+1$ | Floating | No | Yes | NA | NA | NA |
| [16] | 2 OTA and 1 buffer | $0+1$ | Grounded | Yes | No | NA | Experiment | IC |
| [17] | 1 OTA and 2 buffers | $1+1$ | Grounded | Yes | Yes | NA | Experiment | IC |
| [18] | 2 OTA and 1 opamp | $0+1$ | Grounded | Yes | Yes | NA | Experiment | IC |
|  | 2 OTA, 1 opamp, and 1 buffer | $0+1$ | Floating | Yes | Yes | NA | Experiment | IC |
| [19] | 4 VCT | $0+1$ | Floating | Yes | Yes | $\pm 5$ and NA | Both Sim. and Exp. | CD4007 CMOS |
| [20] | 1 CCII | $2+1$ | Grounded | No | No | NA | Simulation | $1.2 \mu \mathrm{~m}$ CMOS |
| [21] | 1 CCII and 1 COA | $2+1$ | Grounded | No | No | $\pm 1.5$ and NA | Simulation | $0.5 \mu \mathrm{~m}$ CMOS |
| [22] | 2 CCII | $2+1$ | Grounded | No | Yes | 5 and NA | Simulation | $1.2 \mu \mathrm{~m}$ CMOS |
| [23] | 4 CCCII | $0+1$ | Floating | Yes | Yes | $\pm 2.5$ and NA | Simulation | BJT |
| [24] | 1 AD844 (Cir. I and II) | $2+1$ | Grounded | No | No | NA | Experiment | IC |
|  | 2 AD844 (Cir. III) | $2+1$ | Grounded | No | No | NA | Experiment | IC |
| [25] | 2 DO-CCII | $2+1$ | Floating | No | Yes | $\pm 2.5 \mathrm{~V}$ and NA | Simulation | BJT AT and T |
| [26] | 1 DVCC and 2 CCCII | $0+1$ | Floating | Yes | Yes | $\pm 2.5$ and 7.3 | Simulation | BJT AT and T |
| [27] | 2 СССТА | $0+1$ | Grounded | Yes | Yes | $\pm 1.5$ and 0.82 | Simulation | BJT AT and T |
| [28] | 1 MCFOA | $2+1$ | Grounded | No | Yes | $\pm 1.5$ and 0.52 | Both Sim. and Exp. | $0.25 \mu \mathrm{~m}$ CMOS and IC |
| [29] | 1 VCG-CCII | $0+1$ | Floating | Yes | Yes | 2 and 0.7 | Simulation | $0.35 \mu \mathrm{~m}$ CMOS |
| [30] | 1 DV-CCTA | $0+1$ | Floating | Yes | Yes | $\pm 1.5$ and 0.48 | Simulation | BJT AT and T |
| [31] | 1 TFTFN | $0+1$ | Floating | Yes | Yes | $\pm 10$ and NA | Simulation | BJT and IC |
| [32] | 3 CCDDCC | $0+1$ | Floating | Yes | Yes | $\pm 1.25$ and NA | Simulation | $0.25 \mu \mathrm{~m}$ CMOS |
| [33] | 1 DXCCI and 2 MOS | $0+1$ | Grounded | Yes | No | $\pm 1.65$ and 0.2 | Simulation | $0.35 \mu \mathrm{~m}$ CMOS |
| [34] | 2 VDCC | $2+1$ | Floating | No | Yes | $\pm 0.9 \mathrm{~V}$ and NA | Simulation | $0.18 \mu \mathrm{~m}$ CMOS |
| [35] | 2 FB-VDBA | $0+1$ | Floating | Yes | Yes | $\pm 1$ and NA | Simulation | $0.35 \mu \mathrm{~m}$ CMOS |
| [36] | 2 DVCC | $2+1$ | Floating | No | No | $\pm 0.75$ and 1.29 | Simulation | $0.13 \mu \mathrm{~m}$ CMOS |
| [37] | 1 VDIBA and 1 MOS | $0+1$ | Grounded | Yes | No | $\pm 0.75$ and 5.27 | Simulation | $0.25 \mu \mathrm{~m}$ CMOS |
| [38] | 1 CCII and 1 buffer | $2+1$ | Grounded | No | No | $\pm 0.9 \mathrm{~V}$ and NA | Experiment | $0.18 \mu \mathrm{~m}$ CMOS |
| [39] | 2 VDBA | $1+1$ | Grounded | Yes | Yes | $\pm 0.75$ and 1.57 | Simulation | CMOS $0.25 \mu \mathrm{~m}$ |
| [40] | 1 CDTA* | $1+1$ | Grounded | Yes | No | NA | Experiment | $0.7 \mu \mathrm{~m}$ CMOS |
|  | 1 CDTA** | $2+1$ | Grounded | No | No | NA | Experiment | $0.7 \mu \mathrm{~m}$ CMOS |
|  | 1 CDTA and $1 \mathrm{DVB}^{* * *}$ | $1+1$ | Floating | Yes | No | NA | Experiment | $0.7 \mu \mathrm{~m}$ CMOS |
|  | 1 CDTA and $1 \mathrm{DVB}^{* * * *}$ | $2+1$ | Floating | No | No | NA | Experiment | $0.7 \mu \mathrm{~m}$ CMOS |
| [41] | 2 VDBA | $0+1$ | Grounded | Yes | No | $\pm 0.75$ and 0.75 | Simulation | $0.25 \mu \mathrm{~m}$ CMOS |
| [42] | 1 FB-VDBA | $1+1$ | Floating | Yes | No | $\pm 0.75$ and 7.4 | Simulation | $0.25 \mu \mathrm{~m}$ CMOS |
| [43] | 2 CFOA | $2+1$ | Grounded | No | No | $\pm 0.75$ and NA | Both Sim. and Exp. | $0.35 \mu \mathrm{~m}$ CMOS and IC |

Table 1: Continued.

| Ref. | ABB | $R+C$ | Floating/grounded | Electronic tune | $K_{c}$ can be set to be greater or less than one | Supply (V) and power consumption ( mW ) | Testing | Technology |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| [44] | 2 CFOA | $2+1$ | Grounded | No | Yes | $\pm 0.9$ and 223 | Both Sim. and Exp. | IC |
| [45] | 1 CCIIITA | $0+1$ | Grounded | Yes | Yes | $\pm 1.5$ and 0.97 | Both Sim. and Exp. | CMOS $0.18 \mu \mathrm{~m}$ and IC |
| [46] | 1 DVB and 1 ECCII | $0+1$ | Grounded | Yes | Yes | $\pm 5$ and 360 | Experiment | IC |
|  | 1 DVB, 1 ECCII, and 1 VGA | $0+1$ | Floating | Yes | Yes | $\pm 5$ and 540 | Experiment | IC |
| [47] | 2 OTRA and 1 buffer | $2+1$ | Grounded | No | Yes | $\pm 0.9$ and 0.83 | Simulation | $0.18 \mu \mathrm{~m}$ CMOS |
| [48] | 2 CFTA | $2+1$ | Grounded | Yes | Yes | $\pm 0.75$ and NA | Both Sim. and Exp. | $0.13 \mu \mathrm{~m}$ CMOS and IC |
| [49] | 1 ICFOA | $2+1$ | Grounded | No | No | $\pm 1.25$ and 0.024 | Both Sim. and Exp. | $0.18 \mu \mathrm{~m}$ CMOS and IC |
| [50] | 2 VCII | $2+1$ | Grounded | No | No | $\pm 1.65$ and 1.5 | Both Sim. and Exp. | $0.35 \mu \mathrm{~m}$ CMOS and IC |
| [51] | 1 VDDDA and 1 MOS | $0+1$ | Grounded | Yes | Yes | $\begin{gathered} \pm 0.9 \text { and } 0.67 \\ \pm 5 \text { and NA } \\ \hline \end{gathered}$ | Both Sim. and Exp. | $0.18 \mu \mathrm{~m}$ CMOS and IC |
| [52] | 1 CFDITA | $2+1$ | Grounded | Yes | No | $\pm 1.25$ and NA | Both Sim. and Exp. | $0.18 \mu \mathrm{~m}$ CMOS and IC |
| [53] | 1 MO-VDTA | $0+1$ | Grounded | Yes | No | $\begin{aligned} & \pm 0.9 \text { and } 0.42 \\ & \pm 12 \text { and NA } \end{aligned}$ | Both Sim. and Exp. | $0.18 \mu \mathrm{~m}$ CMOS and IC |
| [54] | 2 ICFOA | $2+1$ | Floating | No | Yes | $\begin{gathered} \pm 1.25 \text { and } 1.49 \\ \pm 6 \text { and NA } \\ \hline \end{gathered}$ | Both Sim. and Exp. | $0.18 \mu \mathrm{~m}$ CMOS and IC |
| This work | 1 VDDDA | $1+1$ | Grounded | Yes | Yes | $\pm 5$ and 201 | Both Sim. and Exp. | IC |
|  | 1 Zc -VDDDA | $1+1$ | Floating | Yes | Yes | $\pm 5$ and 257 | Both Sim. and Exp. | IC |

[^0]shifters. Finally, Section 5 summarizes the overall content of this paper.

## 2. Principle of the Proposed Circuit

2.1. Overview of $V D D D A$. The voltage differencing differential difference amplifier (VDDDA) is a recent active component that is effectively employed for synthesizing and designing analog signal processing circuits [13]. The VDDDA comprises an operational transconductance amplifier (OTA) and a unity-gain differential difference amplifier (DDA), endowing it with many advantageous characteristics. The OTA section offers several advantages, namely, an expanded frequency range of operation, electronic controllability, and precise parameter adjustment capabilities. Moreover, the DDA demonstrates a high impedance at input voltage terminals, a low impedance at output voltage terminals, and the capacity to execute mathematical computations. Figure 3(a) displays the block diagram of the VDDDA. The diagram depicted in Figure 3(b) represents the VDDDA's equivalent circuit, and internal construction based on commercially available ICs is shown in Figure 3(c) [55].

VDDDA contains high impedance terminals, $v_{+}$, and $v_{-}$, at the OTA section, similar to $z, n$, and $p$ terminals at the VDU section, as depicted in Figures 3(a) and 3(b). The voltage difference between the $v_{+}$and $v_{-}$terminals is transferred to the current at the $z$ terminal through the transconductance, $g_{m}$. A direct current bias imposed externally and defined as $I_{B}$ directly relates to this transconductance. The voltage present at the low output voltage terminal, $w$, is produced by converting the voltage differential between the $z, n$, and $p$ terminals. The following matrix equation can be used to model the port characteristic equation for an ideal VDDDA [13]:

$$
\left(\begin{array}{c}
i_{+}  \tag{1}\\
i_{-} \\
i_{z} \\
i_{n} \\
i_{p} \\
v_{w}
\end{array}\right)=\left(\begin{array}{cccccc}
0 & 0 & 0 & 0 & 0 & 0 \\
0 & 0 & 0 & 0 & 0 & 0 \\
g_{m} & g_{m} & 0 & 0 & 0 & 0 \\
0 & 0 & 0 & 0 & 0 & 0 \\
0 & 0 & 0 & 0 & 0 & 0 \\
0 & 0 & 1 & -1 & 1 & 0
\end{array}\right)\left(\begin{array}{l}
v_{+} \\
v_{-} \\
v_{z} \\
v_{n} \\
v_{p} \\
i_{w}
\end{array}\right)
$$

As shown in Figure 3(c), the VDDDA in this design is implemented utilizing the commercial ICs LT1228 [56] and AD830 [57]. $g_{m}$ for this VDDDA's structure is given by [56]

$$
\begin{equation*}
g_{m}=\frac{I_{B}}{3.87 V_{T}} \tag{2}
\end{equation*}
$$

$V_{T}$ in equation (2) represents thermal voltage. As indicated by equation (2), $g_{m}$ is temperature dependent. At room temperature, $g_{m} \cong 10 I_{B}$. $g_{m}$ may be regulated electronically by adjusting the bias current $I_{B}$. This implies that a microcomputer or microcontroller can easily control circuits based on the LT1228.
2.2. Proposed Grounded Capacitance Multiplier. The proposed grounded capacitance multiplier is depicted in Figure 3. It is constructed of a single VDDDA, a single grounded resistor, and a single floating capacitor. IB, or the bias current, is used to adjust the transconductance gain of the VDDDA electronically. Although the proposed circuit requires a floating capacitor, the metal-oxide-metal (MOM), double poly (poly1-poly2), or metal-insulator-metal (MIM) capacitor processes can be used to fabricate the floating capacitor [58]. Based on equation (1), a circuit analysis can be performed to determine the grounded capacitance multiplier's input impedance (the ratio of $v_{\text {in }}$ to $i_{\text {in }}$ ), which is defined as

$$
\begin{equation*}
Z_{\mathrm{in}}=\frac{v_{\mathrm{in}}}{i_{\mathrm{in}}}=\frac{1}{\mathrm{sg}_{m} \mathrm{RC}} \tag{3}
\end{equation*}
$$

So, from equation (3), it is clear that the proposed circuit realizes a grounded capacitor, and the equation of the equivalent capacitance is given by

$$
\begin{equation*}
C_{\mathrm{eq}}=g_{m} \mathrm{RC} \tag{4}
\end{equation*}
$$

From equation (4), the multiplication factor $\left(K_{C}\right)$ is given by

$$
\begin{equation*}
K_{C}=g_{m} R=10 I_{B} R . \tag{5}
\end{equation*}
$$

It is found from equations (4) and (5) that the original capacitance $(C)$ is multiplied by the multiplication factor, $K_{C}$, which is electronically controlled via the bias current, $I_{B}$. Additionally, the multiplicand can be varied to be greater or less than one.
2.3. Modification as the Floating Capacitance Multiplier. It is well known that the floating type of passive element provides a better winding application than the grounded one. So, the grounded capacitance multiplier designed in Figure 4 is modified to obtain the floating type, as depicted in Figure 1(a). The proposed floating capacitance multiplier consists of a single z-copy VDDDA, a single grounded resistor, and a single floating capacitor. The z-copy VDDDA possesses characteristics identical to VDDDA in all aspects except for the addition of the z-copy terminal. The magnitude of the current at the z-copy terminal is equal to the magnitude of the current at the z-terminal, but they flow in opposite directions. Figure 1(b) illustrates the internal construction of the z-copy VDDDA realized from the commercially available integrated circuits.

Routine procedures analyze the circuit in Figure 1(a) and identify the input impedance as follows:

$$
\begin{equation*}
Z_{\mathrm{in}}=\frac{v_{\mathrm{in} 1}-v_{\mathrm{in} 2}}{i_{\mathrm{in} 1}}=\frac{v_{\mathrm{in} 2}-v_{\mathrm{in} 1}}{i_{\mathrm{in} 2}}=\frac{1}{\mathrm{sg}_{m} \mathrm{RC}} . \tag{6}
\end{equation*}
$$

So, from equation (6), it is clear that the proposed circuit realizes a floating capacitor, and the equations of the equivalent capacitance and the multiplication factor of the floating capacitance multiplier are the same as the grounded one.


Figure 1: (a) Proposed floating capacitance multiplier and (b) internal construction of $\mathrm{Z}_{\mathrm{C}}$-VDDDA.


Figure 2: VDDDA equivalent circuit with parasitic capacitance and resistance [55].


Figure 3: (a) VDDDA symbology and (b) an equivalent representation and (c) internal construction of the VDDDA.


Figure 4: Proposed grounded capacitance multiplier.
2.4. Effect of Voltage Gain Errors. The nonideal characteristics of the VDDDA may impact the performance of the proposed capacitance multipliers. Hence, this section will examine and analyze these nonideal scenarios. To begin with, we will examine the voltage gain errors that occur in the VDU stage of the VDDDA. The VDDDA characteristic with the voltage gain errors is defined by [13]

$$
\left(\begin{array}{c}
i_{+}  \tag{7}\\
i_{-} \\
i_{z} \\
i_{n} \\
i_{p} \\
v_{w}
\end{array}\right)=\left(\begin{array}{cccccc}
0 & 0 & 0 & 0 & 0 & 0 \\
0 & 0 & 0 & 0 & 0 & 0 \\
g_{m} & g_{m} & 0 & 0 & 0 & 0 \\
0 & 0 & 0 & 0 & 0 & 0 \\
0 & 0 & 0 & 0 & 0 & 0 \\
0 & 0 & \beta_{z} & -\beta_{n} & \beta_{p} & 0
\end{array}\right)\left(\begin{array}{l}
v_{+} \\
v_{-} \\
v_{z} \\
v_{n} \\
v_{p} \\
i_{w}
\end{array}\right)
$$

In this context, the symbol $\beta_{z}$ represents the voltage gain error between the $z$ and $w$ terminals, $\beta_{n}$ represents the voltage gain error between the $n$ and $w$ terminals, and $\beta_{p}$ represents the voltage gain error between the $p$ and $w$ terminals. Due to these mistakes, the input impedance of the proposed grounded capacitance multiplier is the same as the input impedance at port $v_{\mathrm{in} 2}$ of the proposed floating capacitance multiplier, where port $v_{\mathrm{in} 2}$ is grounded. This can be shown mathematically as

$$
\begin{equation*}
Z_{\mathrm{in}}^{*}=\left.Z_{\mathrm{in1} 1}^{*}\right|_{v_{\mathrm{in} 2}=0}=\frac{1}{s \beta_{z} g_{m} \mathrm{RC}}+\frac{1}{\beta_{z} g_{m}}-\frac{\beta_{p}}{\beta_{z} g_{m}} \tag{8}
\end{equation*}
$$

The input impedance at port $v_{\text {in2 }}$ of the proposed floating capacitance multiplier, where port $v_{\text {in1 }}$ is grounded, can be given by

$$
\begin{equation*}
\left.Z_{\mathrm{in} 2}^{*}\right|_{v_{\mathrm{in} 1}=0}=\frac{1}{s \beta_{z} g_{m} \mathrm{RC}}+\frac{1}{\beta_{z} g_{m}}-\frac{\beta_{n}}{\beta_{z} g_{m}} \tag{9}
\end{equation*}
$$

The last two nonideal terms $\left(1 / \beta_{z} g_{m}-\beta_{p} / \beta_{z} g_{m}\right)$ in equation (8) and ( $1 / \beta_{z} g_{m}-\beta_{n} / \beta_{z} g_{m}$ ) in equation (9) appear to be the resistance connected in series with the capacitance.

These nonideal terms will affect the workability of the proposed capacitance multipliers in the high-frequency region.
2.5. Effect of Parasitic Elements. Next, we will examine the impact of parasitic impedances on the input and output terminals of the VDDDA. The parasitic impedances present in the circuit include the parallel capacitance $\left(C_{+}\right)$and resistance $\left(R_{+}\right)$at the $v_{+}$terminal, the parallel capacitance ( $C_{-}$) and resistance $\left(R_{-}\right)$at the $v_{-}$terminal, the parallel capacitance $\left(C_{z}\right)$ and resistance $\left(R_{z}\right)$ at the $z$ terminal, the parallel capacitance $\left(C_{n}\right)$ and resistance $\left(R_{n}\right)$ at the $n$ terminal, the parallel capacitance $\left(C_{p}\right)$ and resistance $\left(R_{p}\right)$ at the $p$ terminal, the parallel capacitance $\left(C_{z c}\right)$ and resistance $\left(R_{z c}\right)$ at the $z$-copy terminal (for $Z_{c}$-VDDDA), and the series resistance $\left(r_{w}\right)$ and inductance $\left(L_{w}\right)$ at the low output impedance $w$ terminal as depicted in Figure 2 [55]. For standard VDDDA, there is no $z$-copy terminal, so the parasitic capacitance $C_{z c}$ and resistance $R_{z c}$ are neglected.

At high frequencies, the operation of the proposed circuits is limited by the parasitic capacitances $C_{-}, C_{p}$, and the parasitic resistance, $r_{w}$. The operation frequency of the proposed circuits caused by these parasitic elements is determined by

$$
\begin{equation*}
f_{\mathrm{op}} \ll \frac{1}{2 \pi \sqrt{C\left(C_{-}+C_{p}\right)\left(R / / R_{-} / / R_{p}\right) r_{w}}} \tag{10}
\end{equation*}
$$

Equation (10) reveals a noteworthy discovery: to ensure that the proposed circuits may function effectively at higher frequencies, it is crucial to adjust the capacitance factor through the transconductance $g_{m}$. It is advisable to use a resistor $R$ with a low value to maximize the operational frequency. If the operational frequency of the proposed circuits is less than equation (10), the parasitic capacitances $C_{-}$and $C_{p}$ 's effects are ignored. So, the input impedance of the proposed grounded capacitance multiplier and the input


Figure 5: Simulated AC analyses of VDDDA.
impedance at port $v_{\text {in } 1}$ of the proposed floating capacitance multiplier (where port $v_{\mathrm{in} 2}$ is grounded) can be shown mathematically as

$$
Z_{\mathrm{in}}^{*}=\left.Z_{\mathrm{in} 1}^{*}\right|_{v_{\mathrm{in} 2}=0}=\left\{\begin{array}{c}
\frac{1}{\mathrm{sCg}\left(R / / R_{-} / / R_{p}\right)}+\frac{s L_{w}}{g_{m}\left(R / / R_{-} / / R_{p}\right)}  \tag{11}\\
+\frac{r_{w}}{g_{m}\left(R / / R_{-} / / R_{p}\right)}
\end{array}\right\} / / \frac{1}{\mathrm{sC}_{z}} / / R_{z}
$$

The input impedance at port $v_{\text {in2 }}$ of the proposed floating capacitance multiplier, where port $v_{\text {in } 1}$ is grounded, can be given by

$$
\left.Z_{\mathrm{in} 1}^{*}\right|_{v_{\mathrm{in} 1}=0}=\left\{\begin{array}{c}
\frac{1}{\mathrm{sCg}\left(R / / R_{-} / / R_{p}\right)}+\frac{s L_{w}}{g_{m}\left(R / / R_{-} / / R_{p}\right)}  \tag{12}\\
+\frac{r_{w}}{g_{m}\left(R / / R_{-} / / R_{p}\right)}
\end{array}\right\} / / \frac{1}{s\left(C_{\mathrm{zc}}+C_{n}\right)} / / R_{\mathrm{zc}} / / R_{n}
$$

Equations (11) and (12) reveal that the term in the blanket is the series of capacitance, inductance, and resistance, which is parallel with $C_{z}$ and $R_{z}$ for the grounded one and $C_{z c}, C_{z \mathrm{n}}, R_{z c}$, and $R_{n}$ for the floating one. Equations (11) and (12) align with the study findings discussed in references [59, 60]. The parasitic resistances $R_{z}, R_{z c}$, and $R_{n}$ influence the operation of the proposed capacitance multipliers at low frequencies, according to equations (11) and (12). In contrast, at high frequencies, they are affected by the parasitic inductance $L_{w}$.

## 3. Simulation and Experimental Results

In this section, the grounded and floating capacitance multipliers were tested with the help of the PSpice program and a prototype experiment. The internal schemes of the

VDDDA and $Z_{c}$-VDDDA were made with commercially available integrated circuits (ICs): the LT1228 and the AD830, as shown in Figures 1(b) and 3(c), respectively. In the simulation, the PSpice macromodels of the LT1228 and AD830 discrete components were employed. The circuits were biased with $\pm 5$ VDC power supplies. The performance of the VDDDA was simulated using AC analysis, and the results are shown in Figure 5. The bias current was chosen to be $I_{B}=100 \mu \mathrm{~A}$, leading to a $g_{m}$ value of approximately $0.962 \mathrm{~mA} / \mathrm{V}$. The voltage gain errors $\beta_{z}, \beta_{p}$, and $\beta_{n}$ are 0.993 , 0.995 , and 0.993 , respectively. The -3 dB frequency voltage gains of $v_{w} / v_{z}, v_{w} / v_{p}$, and $v_{w} / v_{n}$ are $59.01 \mathrm{MHz}, 57.54 \mathrm{MHz}$, and 59.01 MHz , respectively. Figure 6(a) depicts the experimental setup for testing the proposed capacitance multipliers. The circuit shown in Figure 6(b) was utilized to assess the magnitude and phase characteristics of the input

(a)

(b)

Figure 6: (a) Experimental setup and (b) impedance testing circuit [51].


Figure 7: The magnitude and phase response of $Z_{\text {in }}$ obtained from the grounded capacitance multiplier.

Table 2: The tested results of the grounded capacitance multiplier at $f=20 \mathrm{kHz}$.

| Parameters | Theory | Simulation | Experiment |
| :--- | :---: | :---: | :---: |
| $Z_{\text {in }}(\mathrm{k} \Omega)$ | 1.59 | 1.65 | 1.66 |
| Phase (degree) | -90.00 | -88.45 | -86.54 |
| Kc | 5.00 | 4.82 | 4.79 |

impedance in the proposed grounded and floating capacitance multipliers, which were obtained from [51]. This circuit uses AD844 as an active component.

The purpose of the circuits is to achieve a multiplication factor, $K_{C}$, of 5 . This is accomplished by configuring the circuits (both grounded and floating types) with an $I_{B}$ value of $250 \mu \mathrm{~A}$, corresponding to a transconductance $\left(g_{m}\right)$ of


Figure 8: The magnitude and phase response of $Z_{\mathrm{in} 2}$ obtained from port $v_{\mathrm{in} 2}\left(v_{\mathrm{in} 1}=0\right)$ of the floating capacitance multiplier.

Table 3: The tested results of the floating capacitance multiplier (only port $v_{\text {in } 2}$ ) at $f=20 \mathrm{kHz}$.

| Parameters | Idea | Simulation | Experiment |
| :--- | :---: | :---: | :---: |
| $Z_{\text {in2 }}(\mathrm{k} \Omega)$ | 1.59 | 1.61 | 1.65 |
| Phase (degree) | -90.00 | -88.51 | -86.38 |
| Kc | 5.00 | 4.94 | 4.80 |

2.5 mS . The bias currents were fine-tuned using the bias resistor $\left(R_{B}\right)$. In order to achieve this, the variable bias resistors were connected between the bias terminal (pin 5) of the LT1228 integrated circuits (ICs) and the ground. The selection of the capacitor and resistor was made with a value of $C=1 \mathrm{nF}$ and $R=2 \mathrm{k} \Omega$. Figure 7 displays the magnitude and phase response of the input impedance obtained from the grounded capacitance multiplier. In a valid frequency range, the experimental magnitude of the input impedance shows an inverse relationship with frequency. On the other hand, the phase response stays close to -90 degrees. The ideal, simulated, and experimental values of $Z_{\text {in }}$, phase, and $K_{c}$ are summarized in Table 2. These values were evaluated explicitly at a frequency of 20 kHz . The power consumption of the grounded capacitance multiplier was measured by the utilization of the PSpice program and experimental measurements, resulting in power values of 201 mW and 225 mW , respectively.

Because the input impedance at port $v_{\text {in } 1}$ of the proposed floating capacitance multiplier (where port $v_{\mathrm{in} 2}=0$ ) is the same as the input impedance of the proposed grounded capacitance multiplier, only the input impedance at port $v_{\text {in2 }}$ of the proposed floating capacitance multiplier was tested. Figure 8 displays the magnitude and phase response of the input impedance obtained from port $v_{\mathrm{in} 2}$ of the floating capacitance multiplier. The ideal, simulated, and experimental
values of $Z_{\text {in }}$, phase, and $K_{c}$ of the floating capacitance multiplier are summarized in Table 3. The power consumption of the floating capacitance multiplier, as determined through simulation and experimentation, was found to be 257 mW and 293 mW , respectively.

The results of multiplication factor-tuning are illustrated in Figure 9. In this result, the $I_{\mathrm{B}}$ values were manipulated at $50 \mu \mathrm{~A}, 125 \mu \mathrm{~A}$, and $250 \mu \mathrm{~A}$. The remaining active and passive element values remain unchanged, as previously stated. With these $I_{\mathrm{B}}$ values, the experimental capacitance multiplier factors were obtained as $1.11,2.59$, and 4.79 , respectively. The result depicted in Figure 9 demonstrates the electronic adjustability of the capacitance multiplier factor, as indicated in equation (5). Sweeping the bias current $I_{\mathrm{B}}$ from $20 \mu \mathrm{~A}$ to $800 \mu \mathrm{~A}$ produced a variation in the experimental multiplication factor that ranged from 0.56 to 13.94 . The corresponding results, along with the theoretical evaluations, are shown in Figure 10. To analyze the effect of variations in passive components on the proposed grounded capacitance multiplier, a Monte Carlo analysis was conducted using a $10 \%$ deviation in passive elements. Figures 11(a) and 11(b) display the magnitude and phase responses of the input impedance after 100 runs, respectively.

## 4. Application Examples

In this section, phase shifters with lagging and leading phases are designed as application examples. The proposed grounded capacitance multiplier was utilized for the lagging phase shifter depicted in Figure 12(a), while the proposed floating capacitance multiplier was employed for the leading phase shifter illustrated in Figure 12(b). The equations of the lagging and leading phase shifters are, respectively, given by


Figure 9: The magnitude of $Z_{\text {in }}$ for different $I_{\mathrm{B}}$ values.


Figure 10: The experimental multiplication factor versus $I_{\mathrm{B}}$.

$$
\begin{equation*}
\theta_{\mathrm{lag}}=-2 \tan ^{-1}\left(2 \pi f R_{2} C_{\mathrm{eq}}\right) \tag{13}
\end{equation*}
$$

and

$$
\begin{equation*}
\theta_{\text {lead }}=180-2 \tan ^{-1}\left(2 \pi f R_{2} C_{\mathrm{eq}}\right) \tag{14}
\end{equation*}
$$

Substituting $C_{\text {eq }}$ in equation (4) into equations (13) and (14), the equations of the lagging and leading phase shifters, respectively, became

$$
\begin{equation*}
\theta_{\mathrm{lag}}=-2 \tan ^{-1}\left(20 \pi f R_{2} \mathrm{RCI}_{B}\right) \tag{15}
\end{equation*}
$$

and

$$
\begin{equation*}
\theta_{\text {lead }}=180-2 \tan ^{-1}\left(20 \pi f R_{2} \mathrm{RCI}_{B}\right) \tag{16}
\end{equation*}
$$

It is seen from equations (15) and (16) that the phase shift is electronically controlled by $I_{B}$.


Figure 11: A Monte Carlo analysis with 100 running for $10 \%$ passive elements changes (a) magnitude (b) phase.

(a)

(b)

Figure 12: (a) The lagging phase shifter and (b) the leading phase shifter.

The lagging phase shifter using the proposed grounded capacitance multiplier depicted in Figure 12(a) was experimentally tested with $\pm 5$ VDC power supplies. The LF351 opamp was employed. The selection of the active and passive elements was made with a value of $I_{B}=150 \mu \mathrm{~A}, C=1 \mathrm{nF}$, $R=2 \mathrm{k} \Omega$ (in capacitance multiplier), $R_{1}=2 \mathrm{k} \Omega$, and $R_{2}=0.33 \mathrm{k} \Omega$. Figure 13 displays the gain and phase response of the lagging phase shifter. Within an acceptable frequency range, the measured and simulated voltage gains are around 0 dB , while the measured and simulated phase shifts with respect to frequency range from 0 degrees to approximately -120 degrees. When the frequency is higher than 300 kHz ,
the measured and simulated responses significantly differ from the expected responses. This is due to the parasitic element and the opamp's gain bandwidth. The output voltage of the lagging phase shifter is demonstrated in Figure 14, where a sinusoidal input waveform with 50 mVp p at 200 kHz was applied. The measured voltage gain is 0.905 ( $9.5 \%$ error), and the measured phase shift is -103.3 degrees ( $0.87 \%$ error). The electronic controllability of the lagging phase shift by varying the bias current $(50 \mu \mathrm{~A}, 100 \mu \mathrm{~A}$, and $150 \mu \mathrm{~A}$ ) is depicted in Figure 15. With these $I_{B}$ values, the experimental phase shifts at $f=100 \mathrm{kHz}$ were obtained as $-24.96^{\circ},-44.57^{\circ}$, and $-61.91^{\circ}$, respectively. The result


Figure 13: The gain and phase response of the lagging phase shifter.


Figure 14: Measured input and output waveforms of the lagging phase shifter.
depicted in Figure 13 demonstrates the electronic adjustability of the lagging phase shift, as indicated in equation (15).

The leading phase shifter was also experimentally tested. The active and passive element selection was the same as the lagging phase shifter, except $R_{2}=0.47 \mathrm{k} \Omega$. Figure 16 displays the gain and phase response of the leading phase shifter. Within an acceptable frequency range, the experimental and simulated voltage gains of the leading phase shifter are around 0 dB , while the experimental and simulated leading phase shifts with respect to a frequency range from 180 degrees to approximately 35 degrees. When the frequency is
higher than 300 kHz , the measured and simulated responses significantly differ from the expected responses. This is due to the parasitic element and the opamp's gain bandwidth. The output voltage of the leading phase shifter is demonstrated in Figure 17, where a sinusoidal input waveform with $50 \mathrm{mVp}-\mathrm{p}$ at 200 kHz was applied. The experimental voltage gain is 0.905 ( $5.19 \%$ error), and the experimental leading phase shift is 57.2 degrees ( $2.83 \%$ error). The electronic controllability of the leading phase shift by varying the bias current is depicted in Figure 18. With these $I_{B} I_{B}$ values, the experimental leading phase shifts at $f=100 \mathrm{kHz}$ were obtained as $145.40^{\circ}, 119.81^{\circ}$, and $99.12^{\circ}$, respectively. The result


Figure 15: The lagging phase tuning by $I_{B}$.


Figure 16: The gain and phase response of the leading phase shifter.


Figure 17: Measured input and output waveforms of the leading phase shifter.


Figure 18: The leading phase tuning by $I_{B}$.
depicted in Figure 16 demonstrates the electronic adjustability of the lagging phase shift, as indicated in equation (16).

## 5. Conclusions

This paper proposes grounded and floating capacitance multipliers. The proposed circuits have a simple structure using a single VDDDA as an active element with one resistor and one capacitor. The floating one is slightly modified from the grounded one by using the Zc -VDDDA, which contains two Z terminals with an opposite-direction current. The multiplication factor of the proposed circuits is electronically adjusted via the bias current. The effect of nonideal VDDDA's properties included voltage and current tracking errors, and parasitic elements were also studied. These nonideal properties had an impact on the proposed circuits' operational frequency range and the accuracy of the capacitance multiplier factor. The parasitic resistances $R_{z}, R_{z c}$, and $R_{n}$ influence the operation of the proposed capacitance multipliers at low frequencies, according to equations (11) and (12). In contrast, at high frequencies, they are affected by the parasitic inductance $L_{w}$. The validity of the proposed capacitance multipliers was verified through the PSpice simulation and experiment using VDDDA built up from the commercially available ICs. The multiplication factor can be electronically adjusted and ranges approximately between 0.56 and 13.94 . The working frequency range reaches nearly three decades. With $\pm 5 \mathrm{~V}$ power supplies, the measured power consumption of the grounded and floating capacitance multipliers is 225 mW and 293 mW , respectively. Additionally, the application examples, such as the lagging and leading phase shifters using the proposed circuits, and their experimental verification were designed and verified to confirm the workability of the proposed capacitance multipliers.

## Data Availability

No data were used to support this study.

## Conflicts of Interest

The authors declare that they have no conflicts of interest.

## Acknowledgments

This research work was supported by KMITL Research and Innovation Services under contract no. KREF016520, King Mongkut's Institute of Technology Ladkrabang (KMITL).

## References

[1] J. Choi, J. Park, W. Kim, K. Lim, and J. Laskar, "High multiplication factor capacitor multiplier for an on-chip PLL loop filter," Electronics Letters, vol. 45, no. 5, pp. 239-240, 2009.
[2] E. Rodriguez-Villegas, A. J. Casson, and P. Corbishley, "A subhertz nanopower low-pass filter," IEEE Transactions on Circuits and Systems II: Express Briefs, vol. 58, no. 6, pp. 351-355, 2011.
[3] M. A. Al-Absi, E. S. Al-Suhaibani, and M. T. Abuelma'atti, "A new compact CMOS C-multiplier," A nalog Integrated Circuits and Signal Processing, vol. 90, no. 3, pp. 653-658, 2017.
[4] X. Jiawei, M. Guy, and P. Merken, "Low-power lock-in amplifier for complex impedance measurement," in Proceedings of the 2019 3rd International Workshop on Advances in sensors and Interfaces, pp. 110-114, IEEE, Otranto (LE), Italy, June 2019.
[5] A. D. Amico, C. Di Natale, M. Mariucci, and G. Baccarani, "Active capacitance multiplication for sensor application," in Proceedings of Italian Conference of Sensors and Microsystems, Lecce, Italy, February 1997.
[6] M. Ghalandarzadeh and S. Afrang, "A new wide tunability MEMS based variable capacitor using two separate electrostatic vertical comb drive actuators complementary to absolute temperature voltage reference," International Journal of Engineering, Transaction B: Applications, vol. 34, no. 11, pp. 2534-2544, 2021.
[7] F. Maloberti, Analog Design for CMOS VLSI Systems, Springer, NY, USA, 2001.
[8] M. Katebi, A. Nasri, S. Toofan, and H. Zolfkhani, "A temperature compensation voltage controlled oscillator using a complementary to absolute temperature voltage reference," International Journal of Engineering, Transaction B: Applications, vol. 32, no. 3, pp. 710-719, 2019.
[9] D. Biolek, R. Senani, V. Biolkova, and Z. Kolka, "Active elements for analog signal processing: classification, review, and new proposals," Radioengineering, vol. 17, no. 4, pp. 15-32, 2008.
[10] R. Senani and D. R. Bhaskar, "New lossy/loss-less synthetic floating inductance configuration realized with only two CFOAs," Analog Integrated Circuits and Signal Processing, vol. 73, no. 3, pp. 981-987, 2012.
[11] R. Senani, D. R. Bhaskar, and P. Kumar, "Two-CFOA-grounded-capacitor first-order all-pass filter configurations with ideally infinite input impedance," AEU-International Journal of Electronics and Communications- International Journal of Electronics and Communications, vol. 137, Article ID 153742, 2021.
[12] M. T. Abuelma'atti and Z. J. Khalifa, "A new CFOA-based negative group delay cascadable circuit," Analog Integrated Circuits and Signal Processing, vol. 95, no. 2, pp. 351-355, 2018.
[13] N. Herencsar, R. Sotner, B. Metin, J. Koton, and K. Vrba, "VDDDA- New 'voltage differencing' device for analog signal processing," in Proceedings of the 2013 8th International Conference on Electrical and Electronics Engineering (ELECO), pp. 17-20, IEEE, Bursa, Turkey, July 2013.
[14] M. A. Siddiqi and M. T. Ahmed, "Simple C-multiplier," IETE Journal of Research, vol. 27, no. 5, pp. 189-190, 1981.
[15] K. Pal, "New inductance and capacitor floatation schemes using current conveyors," Electronics Letters, vol. 17, no. 21, pp. 807-808, 1981.
[16] I. A. Khan and M. Ahmed, "OTA-based integrable voltage/ current- controlled ideal C-Multiplier," Electronics Letters, vol. 22, no. 7, pp. 365-366, 1986.
[17] M. T. Ahmed, I. A. Khan, and T. Parveen, "Wide range electronically tunable component multipliers," International Journal of Electronics, vol. 65, no. 5, pp. 1007-1011, 1988.
[18] M. T. Ahmed, N. Minhaj, and I. Khan, "Novel electronically tunable C-multipliers," Electronics Letters, vol. 31, no. 1, pp. 9-11, 1995.
[19] W. Surakampontorn, K. Kumwachara, V. Riewruja, and C. Surawatpunya, "C-MOS-based integrable electronically tunable floating general impedance inverter," International Journal of Electronics, vol. 82, no. 1, pp. 33-44, 1997.
[20] C. Premont, R. Grisel, and N. Abouchi, "A current conveyor based capacitive multiplier," in Proceedings of the 1997 40th Midwest Symposium on Circuits and Systems, pp. 146-147, IEEE, Sacramento, CA, USA, August 1997.
[21] G. Ferri and S. Pennisri, "A 1.5 V current-mode capacitance multiplier," in Proceedings of the 1998 10th International Conference on Microelectronics, pp. 9-12, IEEE, MonastirTunisia, December 1998.
[22] G. Di Cataldo, G. Ferri, and S. Pennisi, "Active capacitance multipliers using current conveyors," in Proceedings of the 1998 International Symposium on Circuits and Systems (ISCAS), pp. 343-346, IEEE, Monterey, CA, USA, June 1998.
[23] M. T. Abuelma'atti and N. A. Tasadduq, "Electronically tunable capacitance multiplier and frequency-dependent negative-resistance simulator using the current-controlled current conveyor," Microelectronics Journal, vol. 30, no. 9, pp. 869-873, 1999.
[24] A. A. Khan, S. Bimal, K. K. Dey, and S. S. Roy, "Current conveyor based R- and C- multiplier circuits," AEU- International Journal of Electronics and Communications, vol. 56, no. 5, pp. 312-316, 2002.
[25] S. Minaei, E. Yuce, and O. Cicekoglu, "A versatile active circuit for realising floating inductance, capacitance, FDNR and admittance converter," Analog Integrated Circuits and Signal Processing, vol. 47, no. 2, pp. 199-202, 2006.
[26] M. Siripruchyanan and W. Jaikla, "Floating capacitance multiplier using DVCC and CCCIIS," in Proceedings of the 2007 International Symposium on Communications and Information Technologies (ISCIT), pp. 218-221, IEEE, Darling Harbour, October 2007.
[27] P. Silapan, C. Tanaphatsiri, and M. Siripruchyanan, "Current controlled CCTA based-novel grounded capacitance multiplier with temperature compensation," in Proceedings of the 2008 Asia Pacific Conference on Circuits and Systems, pp. 1490-1493, IEEE, Macao, China, December 2008.
[28] E. Yuce and S. Minaei, "A modified CFOA and its applications to simulated inductors, capacitance multipliers, and analog filters," IEEE Transactions on Circuits and Systems I: Regular Papers, vol. 55, no. 1, pp. 266-275, 2008.
[29] A. De Marcellis, G. Ferri, N. C. Guerrini, G. Scotti, V. Stornelli, and A. Trifiletti, "A novel low-voltage low-power
fully differential voltage and current gained CCII for floating impedance simulations," Microelectronics Journal, vol. 40, no. 1, pp. 20-25, 2009.
[30] A. Jantakun, N. Pisutthipong, and M. Siripruchyanun, "Single element based-novel temperature insensitive/electronically controllable floating capacitance multiplier and its application," in Proceedings of the 2010 The International Conference on Electrical Engineering/Electronics, Computer, Telecommunications and Information Technology, pp. 37-41, Chiang Mai, Thailand, May 2010.
[31] W. Jaikla, A. Lahiri, and M. Siripruchyanan, "Capacitance multiplier using tunable four terminal floating nullors," in Proceedings of the 2010 The International Conference on Electrical Engineering/Electronics, Computer, Telecommunications and Information Technology, pp. 42-45, IEEE, Chiang Mai, Thailand, May 2010.
[32] P. Prommee and M. Somdunyakanok, "CMOS-based currentcontrolled DDCC and its applications to capacitance multiplier and universal filter," AEU- International Journal of Electronics and Communications, vol. 65, no. 1, pp. 1-8, 2011.
[33] I. Myderrizi and A. Zeki, "Electronically tunable DXCCIIbased grounded capacitance multiplier," AEU- International Journal of Electronics and Communications, vol. 68, no. 9, pp. 899-906, 2014.
[34] A. Kartci, U. E. Ayten, R. Sotner, and R. Arslanalp, "Electronically tunable VDCC-based floating capacitance multiplier," in Proceedings of the 2015 23rd Signal Processing and Communications Applications Conference (SIU), pp. 24742477, IEEE, Malatya, Turkey, May 2015.
[35] O. Channumsin and W. Tangsirat, "Electronically tunable floating capacitance multiplier using FB-VDBAs," Electronics Letters, vol. 24, no. 3, pp. 365-369, 2016.
[36] H. Alpaslan, "DVCC-based floating capacitance multiplier design," Turkish Journal of Electrical Engineering and Computer Sciences, vol. 25, no. 2, pp. 1334-1345, 2017.
[37] W. Tangsrirat, "Resistorsless tunable capacitance multiplier using single voltage differencing inverting buffered amplifier," Rev Roumaine des Sciences Techniques-Series Electrotechnique et Energetique, vol. 62, no. 1, pp. 72-75, 2017.
[38] A. Yesil, E. Yuce, and S. Minaei, "Grounded capacitance multipliers based on active elements," AEU- International Journal of Electronics and Communications, vol. 79, pp. 243-249, 2017.
[39] P. Moonmuang, T. Pukkalanun, and W. Tangsrirat, "VDBAbased electronically tunable capacitance multiplier with a grounded capacitor," in Proceedings of the 2018 15th International Conference Electrical Engineering/Electronics, Computer Telecommunications and Information Technology, pp. 485-488, IEEE, Chiang Rai, Thailand, July 2018.
[40] D. Biolek, J. Vavra, and A. U. Keskin, "CDTA-based capacitance multipliers," Circuits, Systems, and Signal Processing, vol. 38, no. 4, pp. 1466-1481, 2019.
[41] P. Moonmuang, T. Pukkalanun, and W. Tangsrirat, "Voltage differencing buffered amplifier-based electronically tunable grounded capacitance multiplier," in Proceedings of the 2019 8th International Conference Informatics, Environment, Energy and Applications, pp. 208-211, IEEE, Osaka Japan, March 2019.
[42] W. Tangsrirat and O. Channumsin, "Tunable floating capacitance multiplier using single fully balanced voltage differencing buffered amplifier," Journal of Coттипications Technology and Electronics, vol. 64, no. 8, pp. 797-803, 2019.
[43] R. Verma, N. Pandey, and R. Pandey, "Novel CFOA based capacitance multiplier and its application," AEU-

International Journal of Electronics and Communications, vol. 107, pp. 192-198, 2019.
[44] M. Dogan and E. Yuce, "A new CFOA based grounded capacitance multiplier," AEU- International Journal of Electronics and Communications, vol. 115, pp. 153034-153198, 2020.
[45] S. Singh, N. Pandey, and R. aPandey, "Electronically tunable grounded capacitance multiplier," IETE Journal of Research, vol. 68, no. 4, pp. 1-12, 2022.
[46] R. Sotner, J. Jerabek, L. Polak, and J. Petrzela, "Capacitance multiplier using small values of multiplication factors for adjustability extension and parasitic resistance cancellation technique," IEEE Access, vol. 8, pp. 144382-144392, 2020.
[47] B. C. Nagar and S. K. Paul, "Lossless grounded admittance simulator using OTRA," Analog Integrated Circuits and Signal Processing, vol. 106, no. 3, pp. 649-659, 2021.
[48] E. Ozer, "Electronically tunable CFTA based positive and negative grounded capacitance multipliers," AEU- International Journal of Electronics and Communications, vol. 134, 2021.
[49] T. Yucehan and E. Yuce, "A new grounded capacitance multiplier using a single ICFOA and a grounded capacitor," IEEE Transactions on Circuits and Systems II: Express Briefs, vol. 69, no. 3, pp. 729-733, 2022.
[50] V. Stornelli, L. Safari, G. Barile, and G. Ferri, "A new VCII based grounded positive/negative capacitance multiplier," AEU- International Journal of Electronics and Communications, vol. 137, 2021.
[51] W. Jaikla, P. Huaihongthong, S. Siripongdee, A. Chaichana, and P. Suwanjan, "Single active element based electronically controllable capacitance multiplier," Journal of Circuits, Systems, and Computers, vol. 31, no. 10, 2022.
[52] A. Kumar, D. Singh, and D. Nand, "A novel CFDITA-Based design of grounded capacitance multiplier and its transpose structure," Circuits, Systems, and Signal Processing, vol. 41, no. 10, pp. 5319-5339, 2022.
[53] B. Sakacı and D. Özenli, "A current mode capacitance multiplier employing a single active element based on ArbelGoldminz cells for low frequency applications," Microelectronic Engineering, vol. 288, 2024.
[54] T. Yucehan, "Two inverting CFOA-Based lossless floating immittance simulator," AEU-International Journal of Electronics and Communications, vol. 173, 2024.
[55] W. Jaikla, F. Khateb, T. Kulej, and K. Pitaksuttayaprot, "Universal filter based on compact CMOS structure of VDDDA," Sensors, vol. 21, no. 5, p. 1683, 2021.
[56] Analog, " 100 MHz current feedback amplifier with DC gain control," https://www.analog.com/media/en/technical-docu-mentation/data-sheets/1228fd.pdf.
[57] Analog, "High speed, video difference amplifier," https:// www.analog.com/media/en/technical-documentation/datasheets/ad830.pdf.
[58] G. Komanapalli, R. Pandey, and N. Pandey, "New sinusoidal oscillator configurations using operational transresistance amplifier," International Journal of Circuit Theory and Applications, vol. 47, no. 5, pp. 666-685, 2019.
[59] M. Aghaei Jeshvaghani and M. Dolatshahi, "A new ultra-low power wide tunable capacitance multiplier circuit in subthreshold region for biomedical applications," $A E U$ - International Journal of Electronics and Communications, vol. 177, 2024.
[60] I. Padilla-Cantoya, "Capacitor multiplier with wide dynamic range and large multiplication factor for filter applications," IEEE Transactions on Circuits and Systems II: Express Briefs, vol. 60, no. 3, pp. 152-156, 2013.


[^0]:    NA indicates that information is not available.

